

### Description

The LMAK13P06 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

### General Features

- $V_{DS} = -60V$   $I_D = -13.5A$

$R_{DS(ON)} < 90m\Omega$  @  $V_{GS}=10V$  (Typ.80m $\Omega$ )

### Application

- Brushless motor
- Load switch
- Uninterruptible power supply

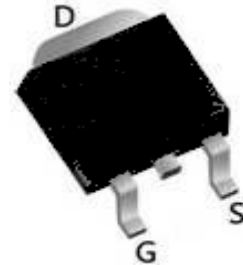
### Package Marking and Ordering Information

Device	Device Marking	Device Package	Reel Size	Tape width	Quantity
LMAK13P06	AP13P06D	TO-252	-	-	2500 units

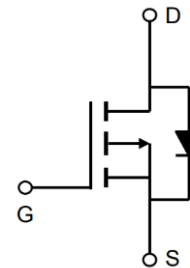
### Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS}$ @ -10V <sup>1</sup>	-13.5	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS}$ @ -10V <sup>1</sup>	-8.3	A
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS}$ @ -10V <sup>1</sup>	-3.3	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS}$ @ -10V <sup>1</sup>	-2.7	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	-26	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	29.8	mJ
$I_{AS}$	Avalanche Current	-24.4	A
$P_D@T_C=25^\circ C$	Total Power Dissipation <sup>4</sup>	31.3	W
$P_D@T_A=25^\circ C$	Total Power Dissipation <sup>4</sup>	2	W
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	62	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	4.0	°C/W

### Dimensions TO-252



### Pin Configuration



## Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-60	---	---	V
ΔBVDSS/ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =-1mA	---	-0.03	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-3A	---	80	90	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2A	---	100	115	
VGS(th)	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-1.2	-1.75	-2.5	V
IDSS	Drain-Source Leakage Current	V <sub>DS</sub> =-48V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =-48V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
IGSS	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
gfs	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-3A	---	8.5	---	S
Q <sub>g</sub>	Total Gate Charge (-4.5V)	V <sub>DS</sub> =-48V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3A	---	12.1	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	2.2	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	6.3	---	
Td(on)	Turn-On Delay Time	V <sub>DD</sub> =-15V, V <sub>GS</sub> =-10V, R <sub>G</sub> =3.3Ω, I <sub>D</sub> =-1A	---	9.2	---	ns
T <sub>r</sub>	Rise Time		---	20.1	---	
Td(off)	Turn-Off Delay Time		---	46.7	---	
T <sub>f</sub>	Fall Time		---	9.4	---	
Ciss	Input Capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1MHz	---	1137	---	pF
Coss	Output Capacitance		---	76	---	
Crss	Reverse Transfer Capacitance		---	50	---	
IS	Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	-13	A
VSD	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A, T <sub>J</sub> =25°C	---	---	-1.2	V

Note :

- 1、 The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、 The data tested by pulsed , pulse width ≅ 300us , duty cycle ≅ 2%
- 3、 The EAS data shows Max. rating . The test condition is V DD =-25V,V GS =-10V,L=0.1mH,IAS =-24A
- 4、 The power dissipation is limited by 150°C junction temperature
- 5、 The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

Typical Electrical and Thermal Characteristics

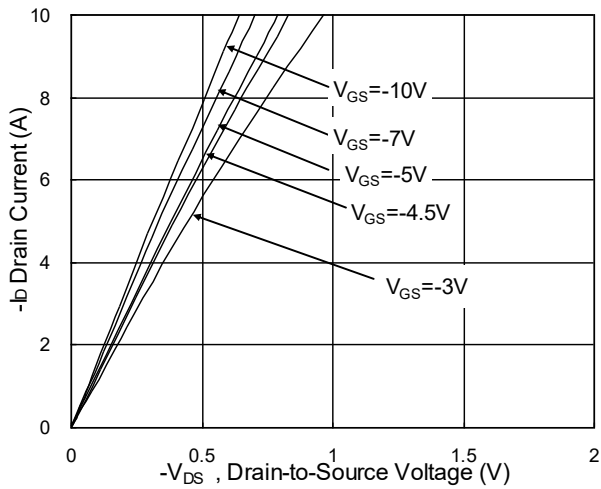


Fig.1 Typical Output Characteristics

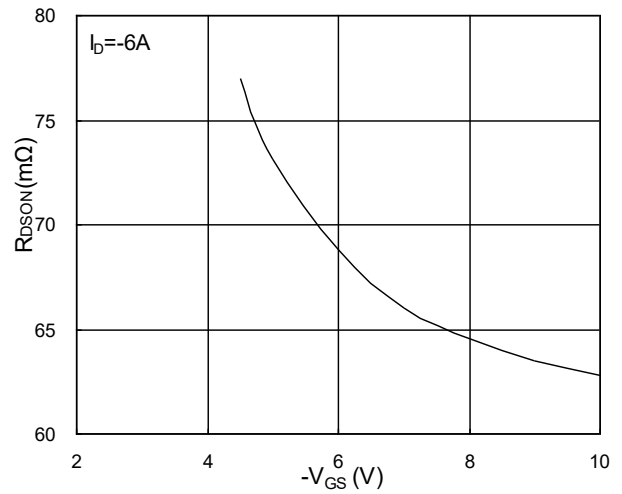


Fig.2 On-Resistance v.s Gate-Source

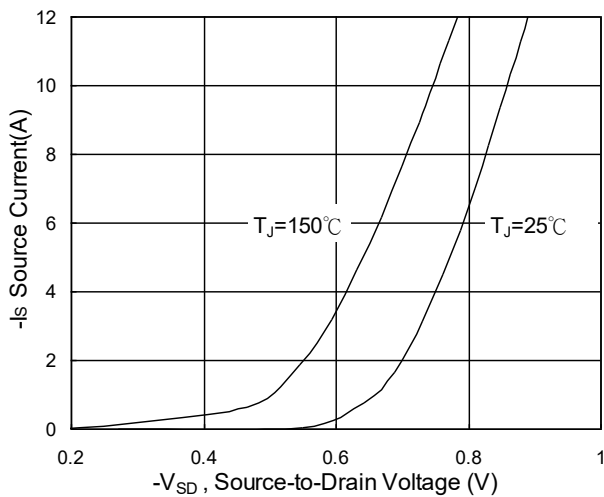


Fig.3 Forward Characteristics of Reverse

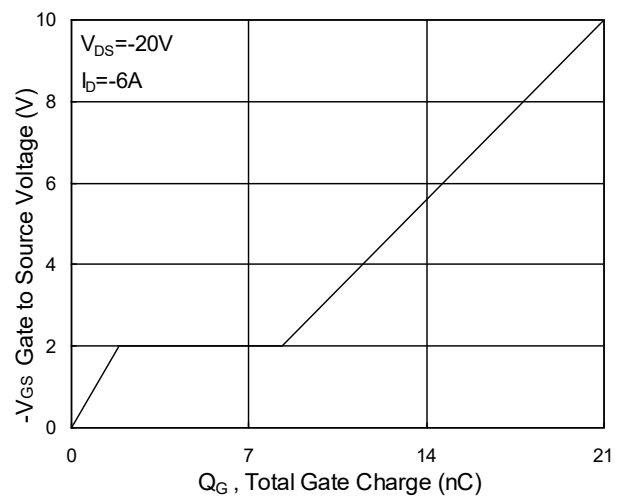


Fig.4 Gate-Charge Characteristics

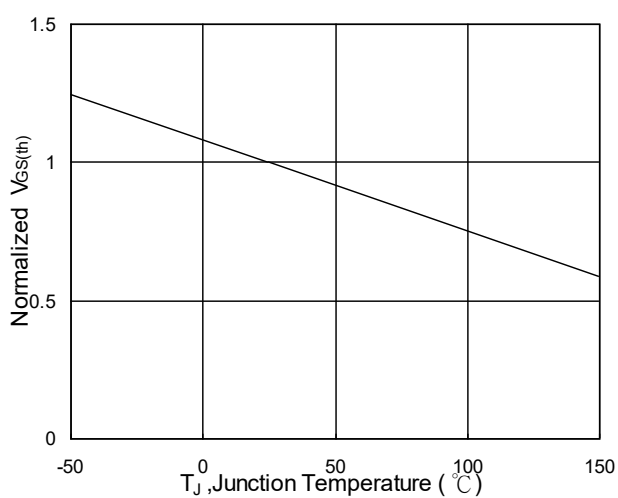


Fig.5 Normalized  $V_{GS(th)}$  v.s  $T_J$

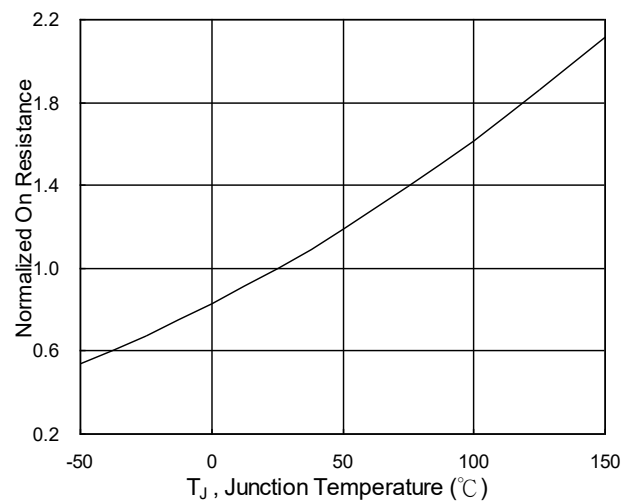
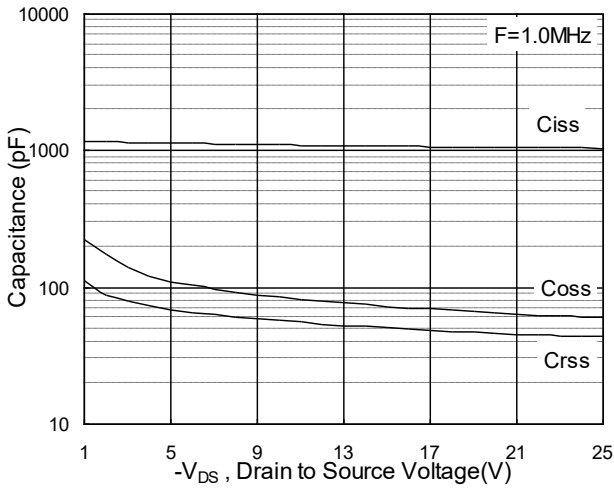
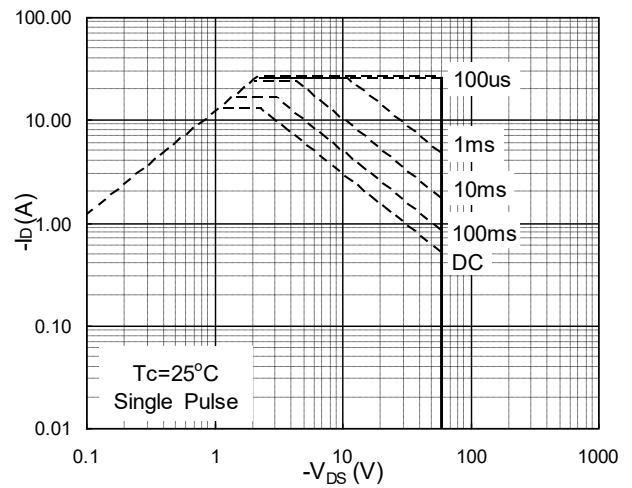


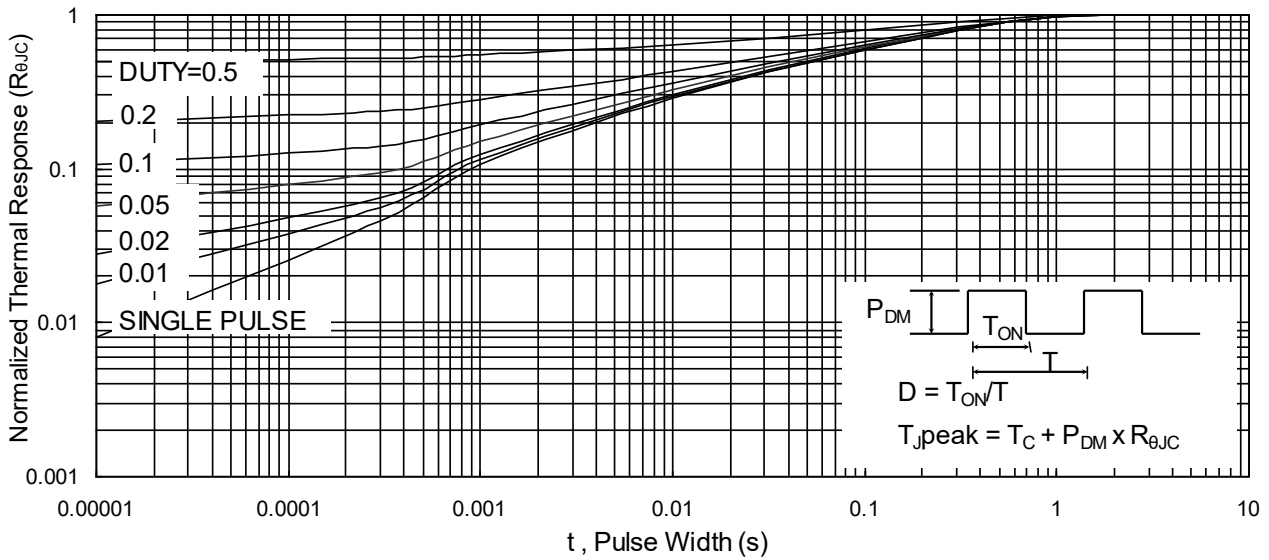
Fig.6 Normalized  $R_{DS(on)}$  v.s  $T_J$



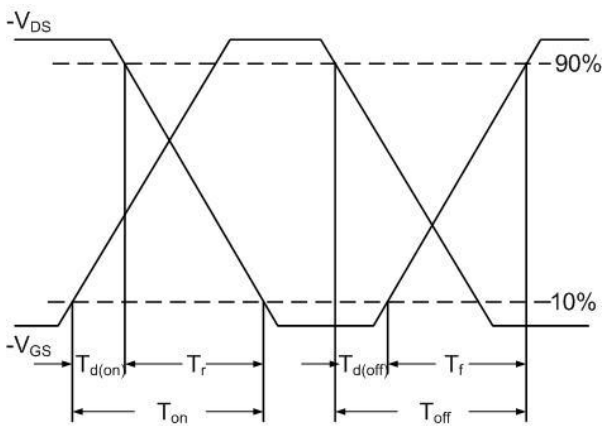
**Fig.7 Capacitance**



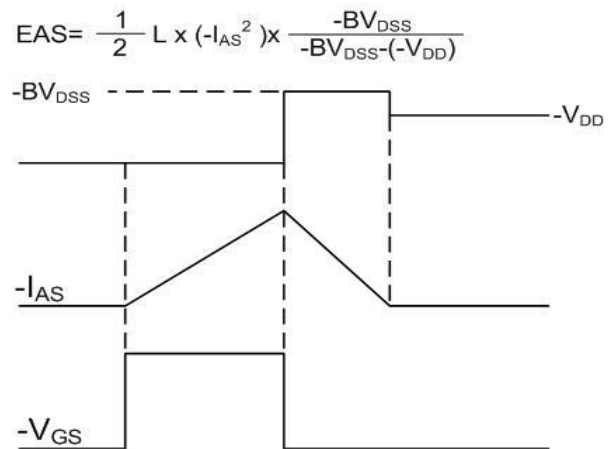
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**

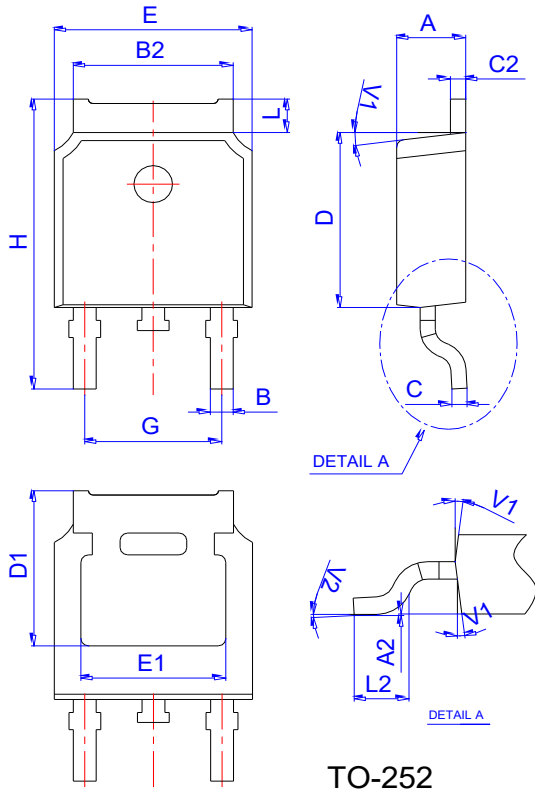


**Fig.10 Switching Time Waveform**



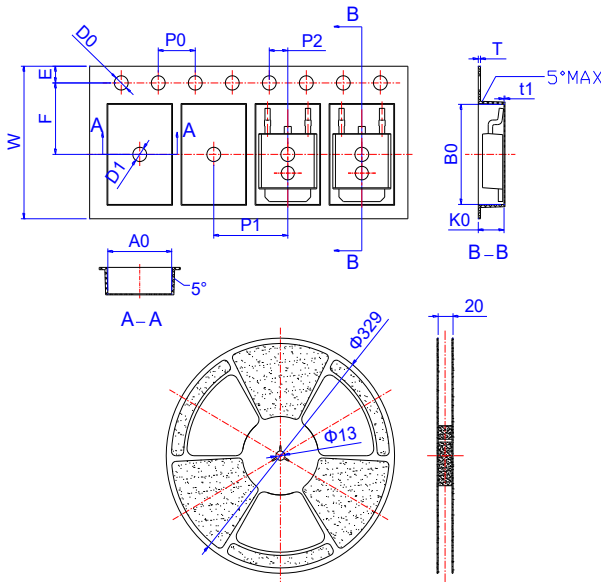
**Fig.11 Unclamped Inductive Switching Waveform**

## Package Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

## Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583